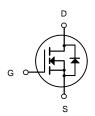


#### Description

The HDMN63D1LT7 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a attery protection Bor in other Switching application.

# D S G

SOT-523



#### N-Channel MOSFET

#### **General Features**

 $V_{DS} = 60V I_D = 0.115A$ 

 $R_{DS(ON)}$  < 3  $\Omega$ @  $V_{GS}$ =10V

## **Application**

Battery protection

Load switch

Uninterruptible power supply

## **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
HDMN63D1LT7	SOT-523	72K	3000

#### Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>DS</sub>	Drain-Source Voltage	60	V
V <sub>G</sub> s	Gate-Source Voltage	±20	٧
l <sub>D</sub>	Drain Current-Continuous	0.115	А
P <sub>D</sub>	Maximum Power Dissipation	0.15	W
TJ,TstG	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$ C
Rеja	Thermal Resistance,Junction-to-Ambient (Note 2)	833	°C/W



#### N-Channel Enhancement Mode MOSFET

# Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

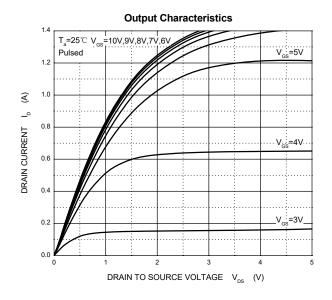
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0 V, I <sub>D</sub> =250 μA	60			V	
Gate-Threshold Voltage	$V_{th(GS)}$	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 μA	1		2.5	V	
Gate-body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =0 V, V <sub>GS</sub> =±20 V			±80	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60 V, V <sub>GS</sub> =0 V			80	nA	
On-state Drain Current	I <sub>D(ON)</sub>	V <sub>GS</sub> =10 V, V <sub>DS</sub> =7 V	500			mA	
Brain Cauras On Basistanas	R <sub>DS(on)</sub>	V <sub>GS</sub> =10 V, I <sub>D</sub> =115mA		1.3	3	Ω	
Drain-Source On-Resistance		V <sub>GS</sub> =4.5V, I <sub>D</sub> =50mA		2	5		
Forward Trans conductance	g <sub>fs</sub>	V <sub>DS</sub> =10 V, I <sub>D</sub> =200mA	80			ms	
Duning and under the second		V <sub>GS</sub> =10V, I <sub>D</sub> =500mA			3.75	V	
Drain-source on-voltage	V <sub>DS(on)</sub>	V <sub>GS</sub> =5V, I <sub>D</sub> =50mA			0.375	V	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =115mA, V <sub>GS</sub> =0 V	0.55		1.2	V	
Input Capacitance	C <sub>iss</sub>				50		
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz			25	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>				5		

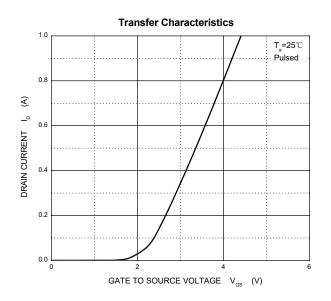
## **Switching Time**

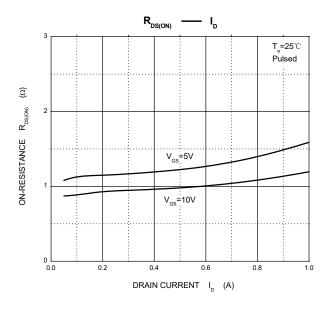
Turn-on Time	t <sub>d(on)</sub>	V <sub>DD</sub> =25 V, R <sub>L</sub> =50Ω		20	20
Turn-off Time	$t_{d(off)}$	$I_D$ =500mA, $V_{GEN}$ =10 V $R_G$ =25 $\Omega$		40	ns

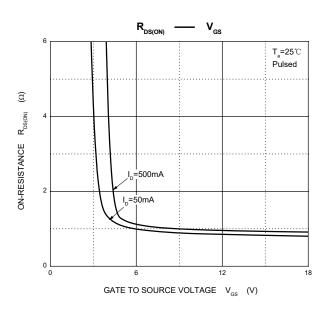


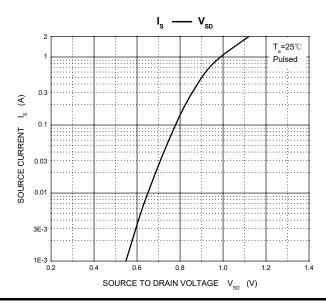
## **Typical Characteristics**





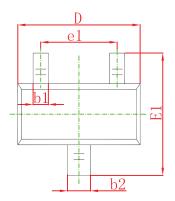


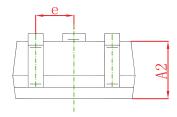


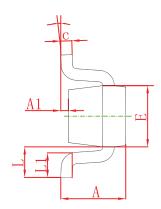




## **SOT-523 Package Information**

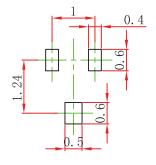






Symbol	Dimensions	In Millimeters	Dimensions In Inches			
	Min.	Max.	Min.	Max.		
Α	0.700	0.900	0.028	0.035		
A1	0.000	0.100	0.000	0.004		
A2	0.700	0.800	0.028	0.031		
b1	0.150	0.250	0.006	0.010		
b2	0.250	0.350	0.010	0.014		
С	0.100	0.200	0.004	0.008		
D	1.500	1.700	0.059	0.067		
E	0.700	0.900	0.028	0.035		
E1	1.450	1.750	0.057	0.069		
е	0.500	0.500 TYP.		0.020 TYP.		
e1	0.900	1.100	0.035	0.043		
Ĺ	0.400 REF.		0.016 REF.			
L1	0.260	0.460	0.010	0.018		
θ	0°	8°	0°	8°		

# **SOT-523 Suggested Pad Layout**



#### Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.



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